

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING BODY  
BIASING CIRCUIT FOR GENERATING FORWARD WELL BIAS  
VOLTAGE OF SUITABLE LEVEL BY USING SIMPLE CIRCUITRY

5

ABSTRACT OF THE DISCLOSURE

10           A semiconductor integrated circuit device has a  
MISFET and a body biasing circuit. The MISFET has a  
source electrode and a drain electrode of a first  
conductivity type and a gate electrode, and the MISFET is  
formed in a well of a second conductivity type. The body  
15           biasing circuit generates a voltage in the well by  
passing a prescribed current in a forward direction into  
a diode which is formed from the well and the source  
electrode of the MISFET.